SEMICONDUCTOR DEVICE, LIQUID CRYSTAL DISPLAY DEVICE, EL DISPLAY DEVICE, SEMICONDUCTOR FILM PRODUCING METHOD, AND SEMICONDUCTOR DEVICE PRODUCING METHOD

Publication number: WO0209192
Publication date: 2002-01-31
Inventor: NISHITANI HIKARU (JP); YAMAMOTO MAKOTO (JP); TAKETOMI YOSHINAO (US)
Applicant: MATSUSHITA ELECTRIC IND CO LTD (JP); NISHITANI HIKARU (JP); YAMAMOTO MAKOTO (JP); TAKETOMI YOSHINAO (US)
Classification:
- international: ***H01L21/20; H01L21/336; H01L21/84; H01L27/12; H01L29/786;*** *G02F1/1368;* **H01L21/02; H01L21/70; H01L27/12; H01L29/66;** G02F1/13; (IPC1-7): H01L29/786; G02F1/1368; H01L21/20; H01L21/336
- European: H01L21/77T; H01L21/20D2; H01L21/336D2B; H01L21/336D2C; H01L27/12; H01L29/786A; H01L29/786B4B; H01L29/786E4C2; H01L29/786E4C4
Application number: WO2001JP06365 20010724
Priority number(s): JP20000222275 20000724; JP20000322301 20001023

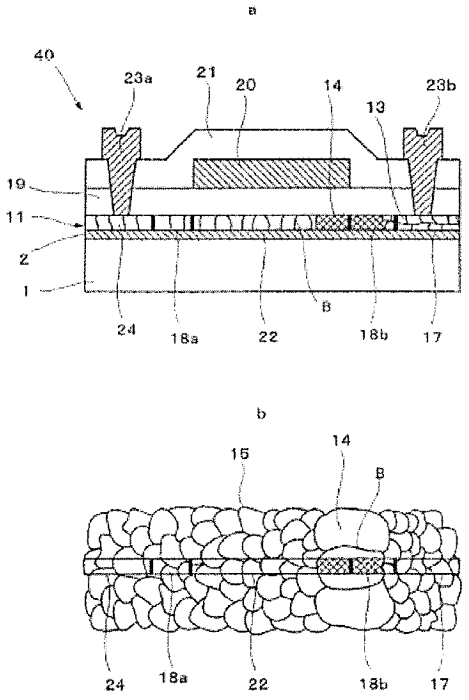
Also published as:
US6906346 (B2)
US2004248386 (A1)
TW515103B (B)

Cited documents:
JP7086604
JP11274502
JP62193178
JP6151305
JP5326402
more >>

Report a data error here

Abstract of **WO0209192**

A semiconductor device characterized by comprising a thin film transistor (40) having a multicrystal semiconductor layer (11), the semiconductor layer (11) containing a channel region (22), high-concentration impurity regions (24, 17) positioned on opposite sides of the channel region (22), and low-concentration impurity regions (18a, 18b) positioned between the channel region (22) and the high-concentration impurity regions (24, 17) and having a lower impurity concentration than that of the high-concentration impurity regions (24, 17), wherein the particle size of crystals (14) at least part of which are present in the low-concentration impurity region (18b) is greater than that of other crystals (15).



Data supplied from the ***esp@cenet*** database - Worldwide